

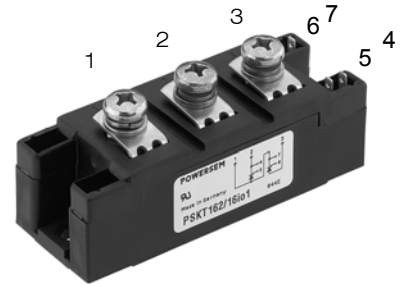
Thyristor Modules Thyristor/Diode Modules

PSKT 162
PSKH 162

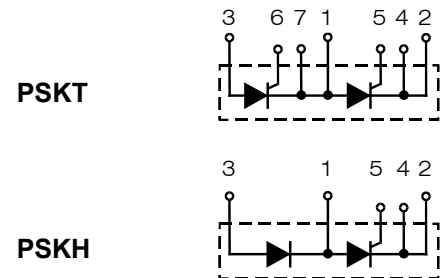
$I_{TRMS} = 2x 300 A$
 $I_{TAVM} = 2x 190 A$
 $V_{RRM} = 800-1800 V$

Preliminary Data Sheet

V_{RSM}	V_{RRM}	Type	
V_{DSM}	V_{DRM}	Version 1	
V	V	Version 1	Version 1
900	800	PSKT 162/08io1	PSKH 162/08io1
1300	1200	PSKT 162/12io1	PSKH 162/12io1
1500	1400	PSKT 162/14io1	PSKH 162/14io1
1700	1600	PSKT 162/16io1	PSKH 162/16io1
1900	1800	PSKT 162/18io1	PSKH 162/18io1



Symbol	Test Conditions	Maximum Ratings	
I_{TRMS}^1 I_{FRMS} I_{TAVM}^2 I_{FAVM}	$T_{VJ} = T_{VJM}$ $T_C = 80^\circ C; 180^\circ$ sine $T_C = 85^\circ C; 180^\circ$ sine	300 190 181	A A A
I_{TSM}^1 I_{FSM}	$T_{VJ} = 45^\circ C;$ $V_R = 0$ $t = 10$ ms (50 Hz), sine $t = 8.3$ ms (60 Hz), sine	6000 6400	A A
	$T_{VJ} = T_{VJM}$ $V_R = 0$ $t = 10$ ms (50 Hz), sine $t = 8.3$ ms (60 Hz), sine	5250 5600	A A
ji^2dt	$T_{VJ} = 45^\circ C$ $V_R = 0$ $t = 10$ ms (50 Hz), sine $t = 8.3$ ms (60 Hz), sine	180 000 170 000	A ² s A ² s
	$T_{VJ} = T_{VJM}$ $V_R = 0$ $t = 10$ ms (50 Hz), sine $t = 8.3$ ms (60 Hz), sine	137 000 128 000	A ² s A ² s
$(di/dt)_{cr}$	$T_{VJ} = T_{VJM}$ $f = 50$ Hz, $t_p = 200$ μ s $V_D = 2/3 V_{DRM}$ $I_G = 0.5$ A $di_G/dt = 0.5$ A/ μ s	repetitive, $I_T = 500$ A non repetitive, $I_T = 500$ A	150 500 A/ μ s A/ μ s
$(dv/dt)_{cr}$	$T_{VJ} = T_{VJM}$ $R_{GK} = \infty$; method 1 (linear voltage rise)	$V_{DR} = 2/3 V_{DRM}$	1000 V/ μ s
P_{GM}	$T_{VJ} = T_{VJM}$ $I_T = I_{TAVM}$	$t_p = 30$ μ s $t_p = 500$ μ s	120 60 8 W W W
P_{GAV}			8 W
V_{RGM}			10 V
T_{VJ}			-40...+125 $^\circ C$
T_{VJM}			125 $^\circ C$
T_{stg}			-40...+125 $^\circ C$
V_{ISOL}	50/60 Hz, RMS $I_{ISOL} \leq 1$ mA	$t = 1$ min $t = 1$ s	3000 3600 V~ V~
M_d	Mounting torque (M6) Terminal connection torque (M6)	2.25-2.75/20-25 4.5-5.5/40-48	Nm/lb.in. Nm/lb.in.
Weight	Typical including screws	125	g



Features

- International standard package
- Direct copper bonded Al_2O_3 -ceramic base plate
- Planar passivated chips
- Isolation voltage 3600 V~
- UL registered, E 148688
- Keyed gate/cathode twin pins

Applications

- Motor control
- Power converter
- Heat and temperature control for industrial furnaces and chemical processes
- Lighting control
- Contactless switches

Advantages

- Space and weight savings
- Simple mounting with two screws
- Improved temperature and power cycling capability
- Reduced protection circuits

Data according to IEC 60747 and refer to a single thyristor/diode unless otherwise stated.

Symbol	Test Conditions	Characteristic Values
I_{RRM}, I_{DRM}	$T_{VJ} = T_{VJM}; V_R = V_{RRM}; V_D = V_{DRM}$	10 mA
V_T, V_F	$I_T, I_F = 300 \text{ A}; T_{VJ} = 25^\circ\text{C}$	1.25 V
V_{T0}	For power-loss calculations only ($T_{VJ} = 125^\circ\text{C}$)	0.88 V
r_T		1.15 mΩ
V_{GT}	$V_D = 6 \text{ V}; T_{VJ} = 25^\circ\text{C}$	2.5 V
	$T_{VJ} = -40^\circ\text{C}$	2.6 V
I_{GT}	$V_D = 6 \text{ V}; T_{VJ} = 25^\circ\text{C}$	150 mA
	$T_{VJ} = -40^\circ\text{C}$	200 mA
V_{GD}	$T_{VJ} = T_{VJM}; V_D = 2/3 V_{DRM}$	0.2 V
I_{GD}		10 mA
I_L	$T_{VJ} = 25^\circ\text{C}; t_p = 30 \mu\text{s}; V_D = 6 \text{ V}$ $I_G = 0.5 \text{ A}; di_G/dt = 0.5 \text{ A}/\mu\text{s}$	300 mA
I_H	$T_{VJ} = 25^\circ\text{C}; V_D = 6 \text{ V}; R_{GK} = \infty$	200 mA
t_{gd}	$T_{VJ} = 25^\circ\text{C}; V_D = 1/2 V_{DRM}$ $I_G = 0.5 \text{ A}; di_G/dt = 0.5 \text{ A}/\mu\text{s}$	2 μs
t_q	$T_{VJ} = T_{VJM}; I_T = 300 \text{ A}, t_p = 200 \text{ ms}; -di/dt = 10 \text{ A}/\mu\text{s typ.}$ $V_R = 100 \text{ V}; dv/dt = 20 \text{ V}/\mu\text{s}; V_D = 2/3 V_{DRM}$	150 μs
Q_S	$T_{VJ} = T_{VJM}; I_T, I_F = 300 \text{ A}, -di/dt = 50 \text{ A}/\mu\text{s}$	550 μC
I_{RM}		235 A
R_{thJC}	per thyristor/diode; DC current per module	0.155 K/W
R_{thJK}	per thyristor/diode; DC current per module	0.225 K/W
	other values see Fig. 8/9	0.0775 K/W 0.1125 K/W
d_s	Creepage distance on surface	12.7 mm
d_A	Strike distance through air	9.6 mm
a	Maximum allowable acceleration	50 m/s ²

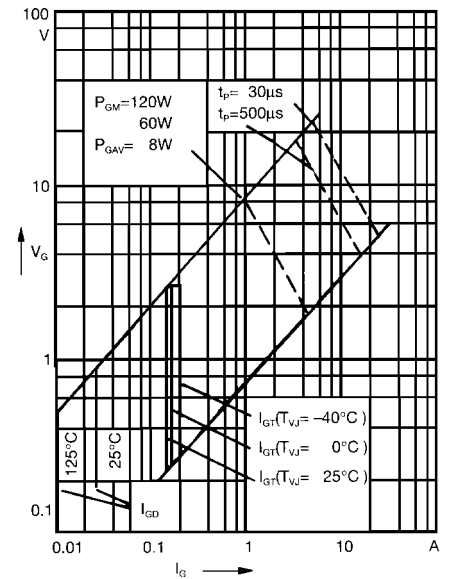


Fig. 1 Gate trigger characteristics

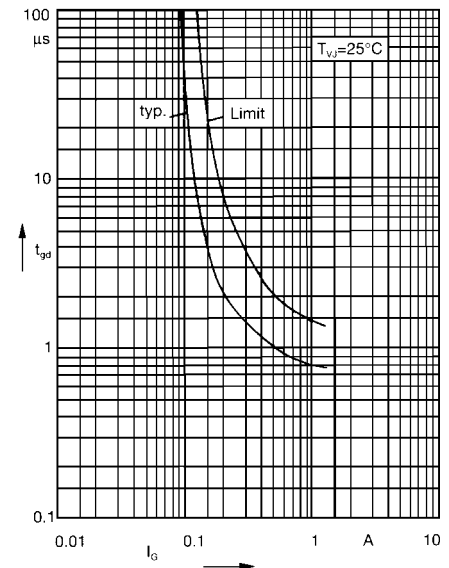
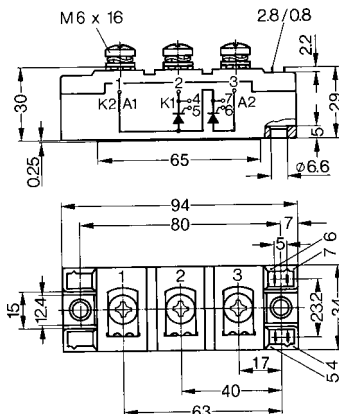


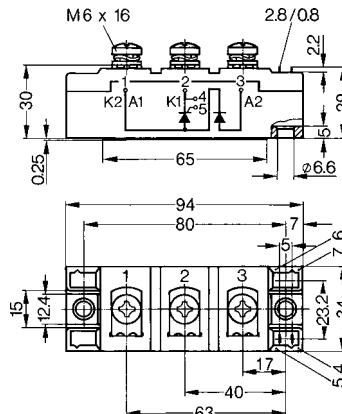
Fig. 2 Gate trigger delay time

Dimensions in mm (1 mm = 0.0394")

PSKT Version 1



PSKH Version 1



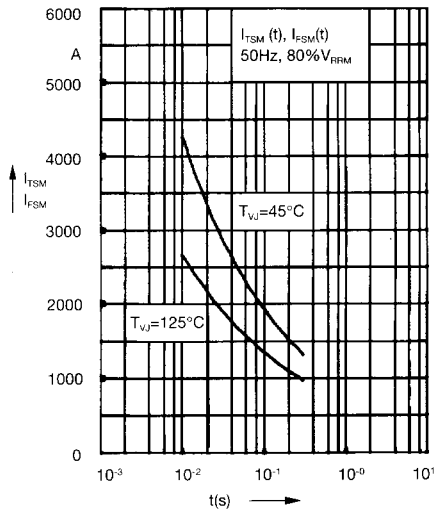


Fig. 3 Surge overload current
 I_{TSM} , I_{FSM} : Crest value, t: duration

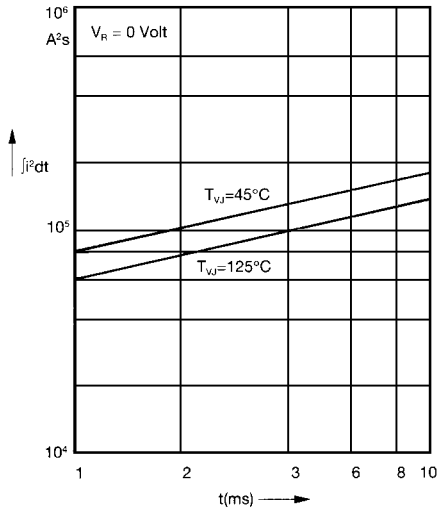


Fig. 4 j^2dt versus time (1-10 ms)

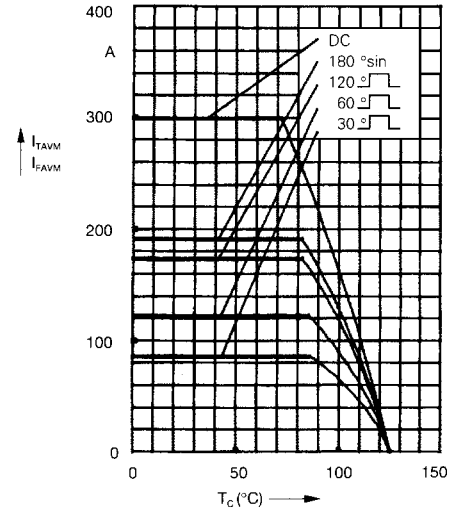


Fig. 4a Maximum forward current at case temperature

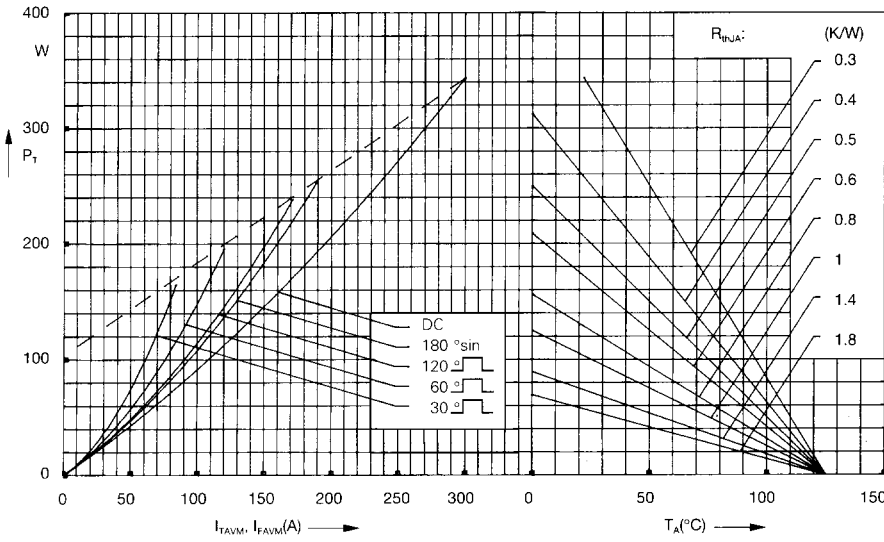


Fig. 5 Power dissipation versus on-state current and ambient temperature (per thyristor or diode)

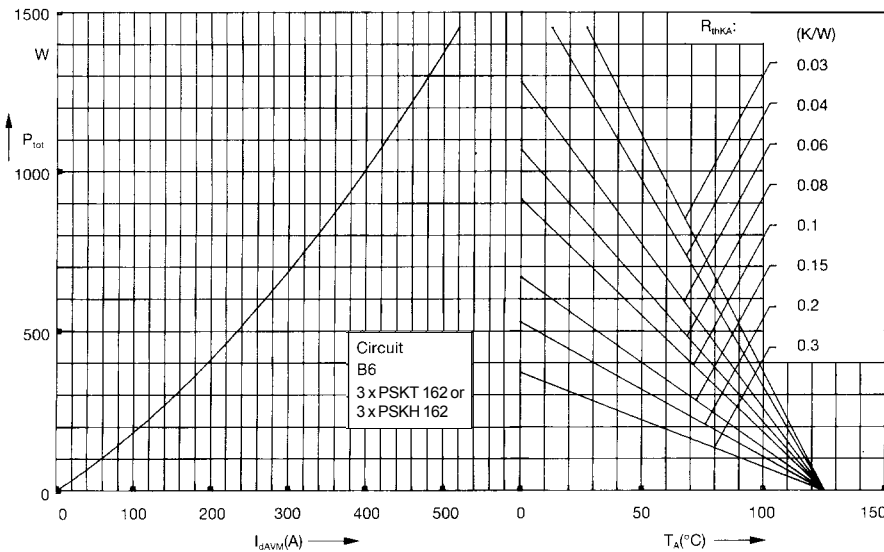


Fig. 6 Three phase rectifier bridge:
 Power dissipation versus direct output current and ambient temperature

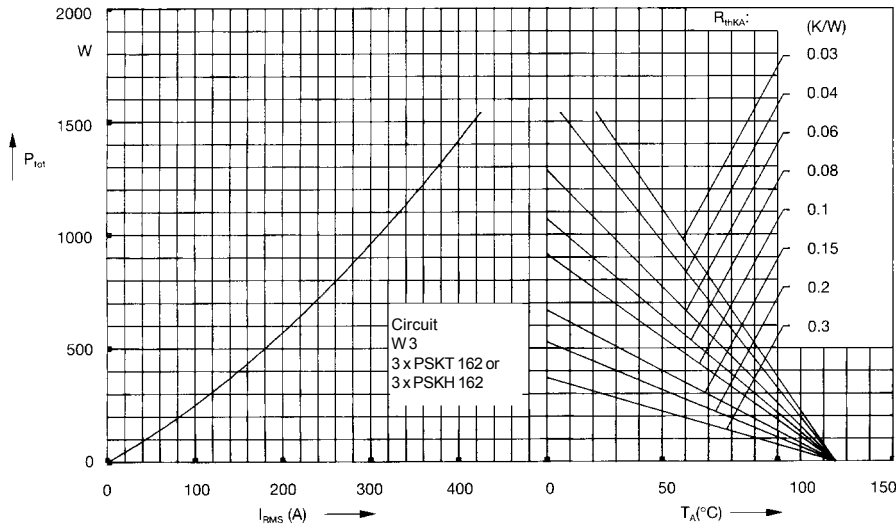


Fig. 7 Three phase AC-controller: Power dissipation versus RMS output current and ambient temperature

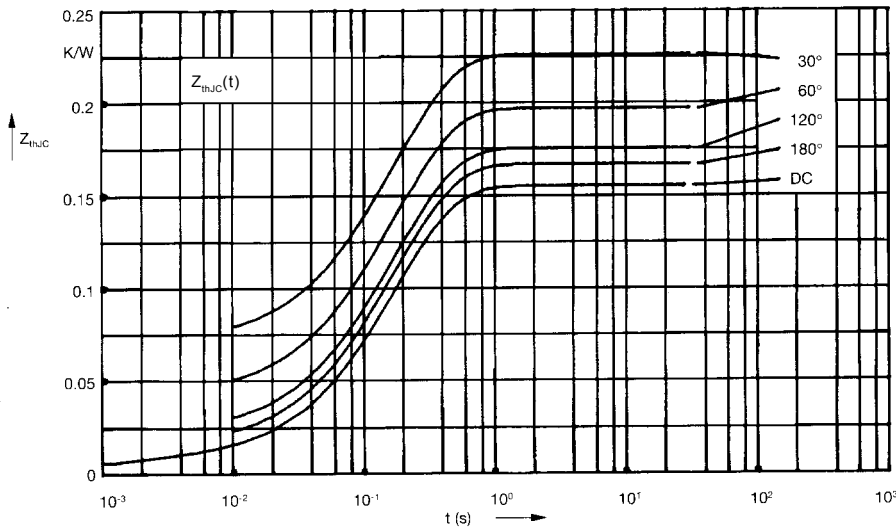


Fig. 8 Transient thermal impedance junction to case (per thyristor or diode)

R_{thJC} for various conduction angles d:

d	R_{thJC} (K/W)
DC	0.155
180°	0.167
120°	0.176
60°	0.197
30°	0.227

Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.0072	0.001
2	0.0188	0.08
3	0.129	0.2

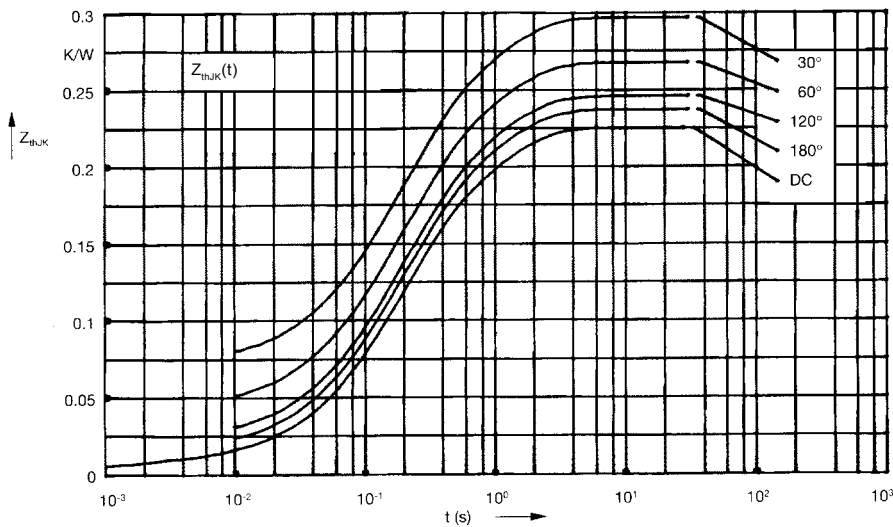


Fig. 9 Transient thermal impedance junction to heatsink (per thyristor or diode)

R_{thJK} for various conduction angles d:

d	R_{thJK} (K/W)
DC	0.225
180°	0.237
120°	0.246
60°	0.267
30°	0.297

Constants for Z_{thJK} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.0072	0.001
2	0.0188	0.08
3	0.129	0.2
4	0.07	1.0